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November 2013

FDB28N30

N-Channel UniFETTM MOSFET 300 V, 28 A, 129 m Ω

Features

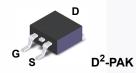
- $R_{DS(on)}$ = 108 $m\Omega$ (Typ.) @ V_{GS} = 10 V, I_D = 14 A
- Low Gate Charge (Typ. 39 nC)
- Low C_{rss} (Typ. 35 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

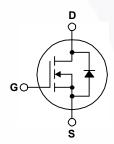
Applications

- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FDB28N30	Unit
V _{DSS}	Drain to Source Voltage		300	V
V _{GSS}	Gate to Source Voltage		±30	V
	Drain Current - Continuous (T _C = 25°C)		28	А
ID	Diamounem	- Continuous (T _C = 100°C)	19	A
I _{DM}	Drain Current	- Pulsed (Note	1) 112	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		2) 588	mJ
I _{AR}	Avalanche Current	(Note	1) 28	Α
E _{AR}	Repetitive Avalanche Ene	ergy (Note	1) 25	mJ
dv/dt	Peak Diode Recovery dv/	'dt (Note	3) 4.5	V/ns
D	Dower Dissipation	$(T_C = 25^{\circ}C)$	250	W
Power Dissipation		- Derate above 25°C	2.0	W/°C
T _J , T _{STG}	Operating and Storage Te	emperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDB28N30	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in ² Pad of 2-oz Copper), Max.	40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB28N30	FDB28N30	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	300	-	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.4	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 300 V, V _{GS} = 0 V	-	-	1	^
I _{DSS}		$V_{DS} = 240 \text{ V}, T_C = 125^{\circ}\text{C}$	-	-	10	μА
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 14 A	-	0.108	0.129	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 14 A	ı	24.8	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V 0.V	-	1690	2250	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	305	405	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112	-\	35	50	pF
Q_g	Total Gate Charge at 10V	V _{DS} = 240 V, I _D = 28 A,	-	39	50	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	12	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note	- 4)	17	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	35	80	ns
t _r		$V_{DD} = 150 \text{ V}, I_D = 28 \text{ A},$	-	135	280	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω	-	79	168	ns
t _f	Turn-Off Fall Time	(Note 4)	-	69	148	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current			-	28	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	112	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 28 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 28 A,	-	279	-	ns
Q _{rr}	Reverse Recovery Charge	$V_{GS} = 0 \text{ V, } I_{SD} = 28 \text{ A,}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	2.7	-	μC

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 1.5 mH, I $_{AS}$ = 28 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. I_{SD} \leq 28 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_DSS, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

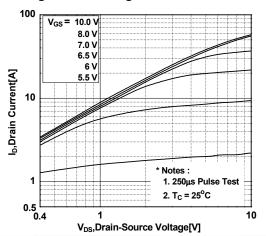


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

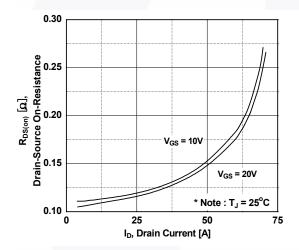


Figure 5. Capacitance Characteristics

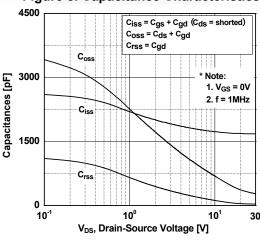


Figure 2. Transfer Characteristics

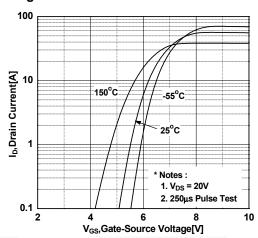


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

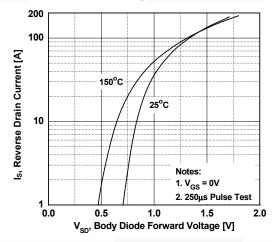
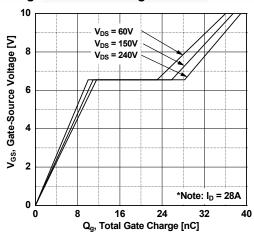
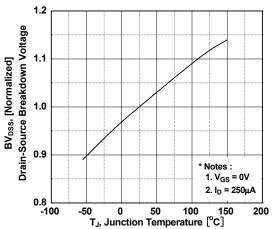


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature



vs. Temperature 3.0

Figure 8. On-Resistance Variation

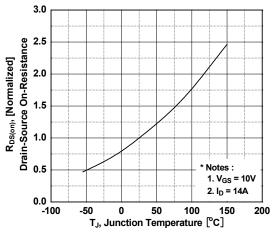


Figure 9. Maximum Safe Operating Area

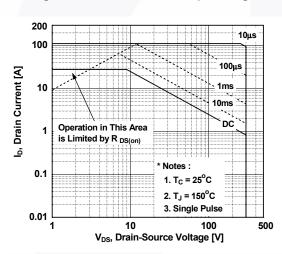


Figure 10. Maximum Drain Current vs. Case Temperature

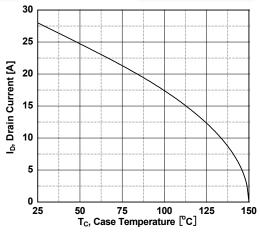
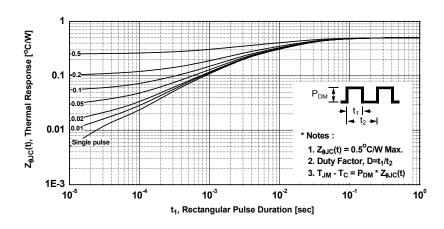


Figure 11. Transient Thermal Response Curve



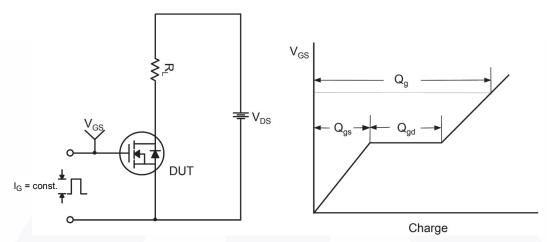


Figure 12. Gate Charge Test Circuit & Waveform

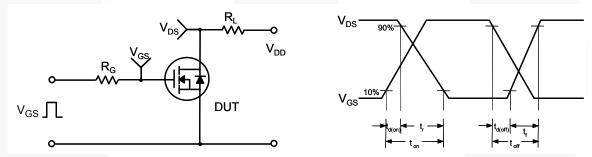


Figure 13. Resistive Switching Test Circuit & Waveforms

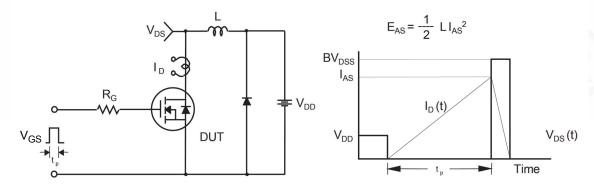


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

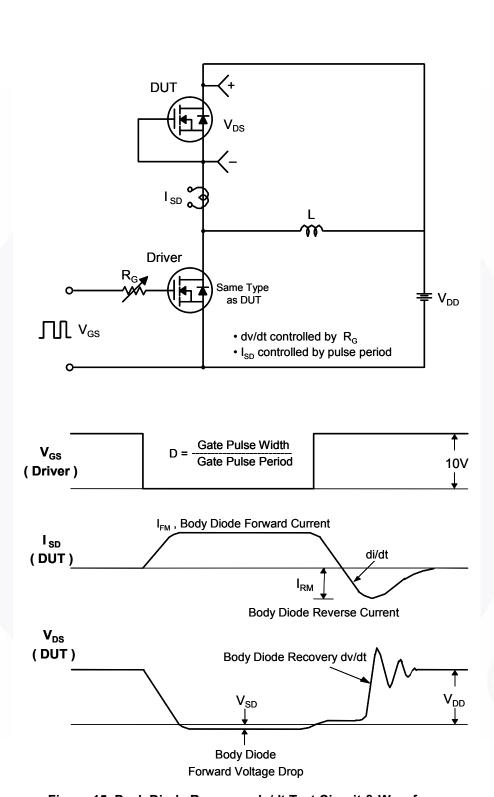


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

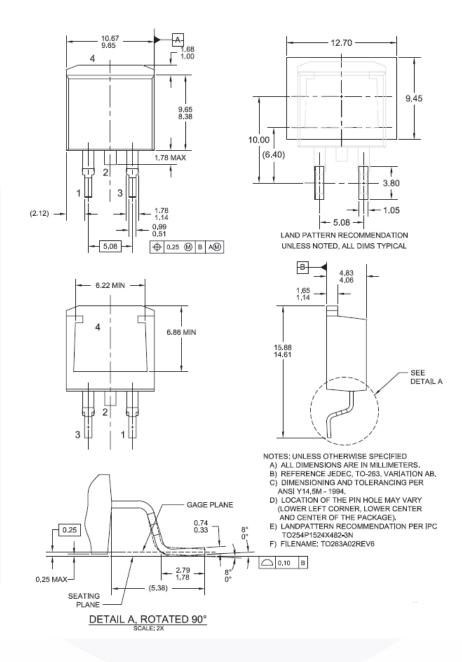


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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